ESD Protection Diode

Micro-Packaged Diodes for ESD Protection

ESDM3032

The ESDM3032 is designed to protect voltage sensitive components that require low capacitance from ESD and transient voltage events. Excellent clamping capability, low capacitance, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium.

Features

- Low Clamping Voltage
- Small Body Outline Dimensions: 0.62 mm x 0.32 mm
- Low Body Height: 0.3 mm
- Stand-off Voltage: 3.3 V
- IEC61000-4-2 Level 4 ESD Protection
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- µSD Card Protection
- Audio Line
- GPIO

MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
IEC 61000-4-2 (ESD) Contact Air		±30 ±30	kV	
Total Power Dissipation on FR–5 Board (Note 1) @ $T_A = 25^{\circ}C$ Thermal Resistance, Junction–to–Ambient	Ρ _D R _{θJA}	250 400	mW °C/W	
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C	
Lead Solder Temperature – Maximum (10 Second Duration)	ΤL	260	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. $FR-5 = 1.0 \times 0.75 \times 0.62$ in.

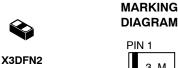
See Application Note AND8308/D for further description of survivability specs.



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CASE 152AF

= Specific Device Code 3

= Date Code М

ORDERING INFORMATION

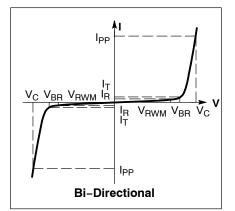
Device	Package	Shipping [†]		
ESDM3032MXT5G	X3DFN2 (Pb–Free)	10000 / Tape & Reel		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

	,
Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ I _{PP}
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
Ι _Τ	Test Current



*See Application Note AND8308/D for detailed explanations of datasheet parameters.

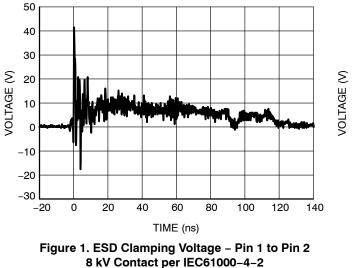
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

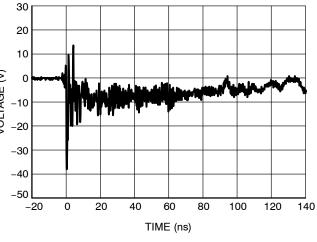
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V _{RWM}	I/O Pin to GND			3.3	V
Breakdown Voltage	V _{BR}	I _T = 1 mA, I/O Pin to GND	4.1		5.7	V
Reverse Leakage Current	I _R	V _{RWM} = 3.3 V, I/O Pin to GND			100	nA
Clamping Voltage TLP (Note 2)	V _C	$I_{PP} = 8 \text{ A} $ $ \begin{cases} \text{IEC } 61000-4-2 \text{ Level } 2 \text{ equivalent} \\ (\pm 4 \text{ kV Contact}, \pm 8 \text{ kV Air}) \end{cases} $		7.2		V
		$I_{PP} = 16 A \\ \left. \begin{array}{c} \text{IEC } 61000 - 4 - 2 \text{ Level 4 equivalent} \\ (\pm 8 \text{ kV Contact}, \pm 16 \text{ kV Air}) \end{array} \right.$		8.5		V
Reverse Peak Pulse Current	I _{PP}	IEC61000-4-5 (8/20 μs)	7.5	8.5		А
Clamping Voltage (8/20 µs) (Note 3)	V _C	I _{PP} = 7.5 A		8.5	9.7	V
Dynamic Resistance	R _{DYN}	100 ns TLP Pulse		0.16		Ω
Junction Capacitance	CJ	V _R = 0 V, f = 1 MHz		8.5	10	pF

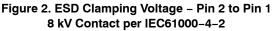
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. ANSI/ESD STM5.5.1 – Electrostatic Discharge Sensitivity Testing using Transmission Line Pulse (TLP) Model. TLP conditions: Z₀ = 50 Ω, t_p = 100 ns, t_r = 1 ns, averaging window; t₁ = 70 ns to t₂ = 90 ns.
 3. Non-repetitive current pulse at T_A = 25°C, per IEC61000–4–5 waveform.

TYPICAL CHARACTERISTICS







ESDM3032

TYPICAL CHARACTERISTICS

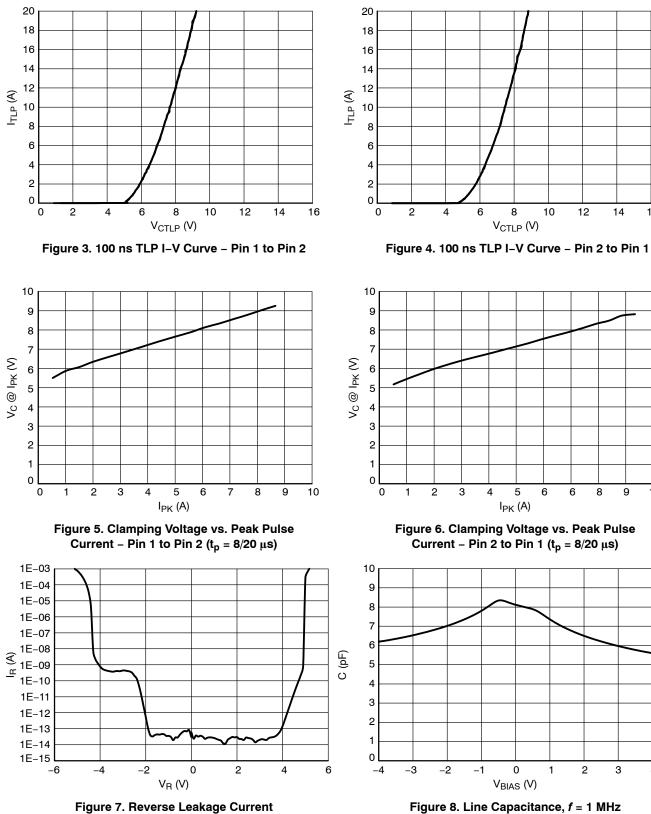


Figure 8. Line Capacitance, *f* = 1 MHz

16

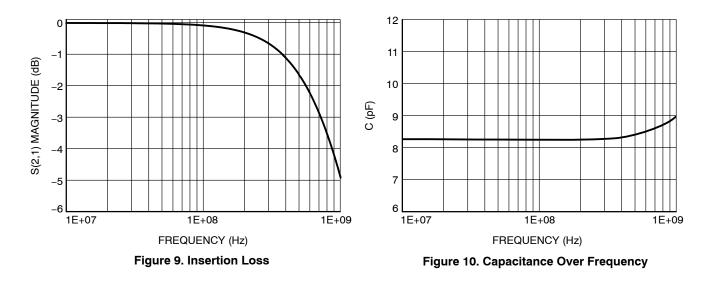
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ESDM3032

TYPICAL CHARACTERISTICS



IEC 61000-4-2 Spec.

Level	Test Volt- age (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

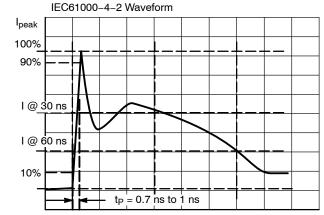
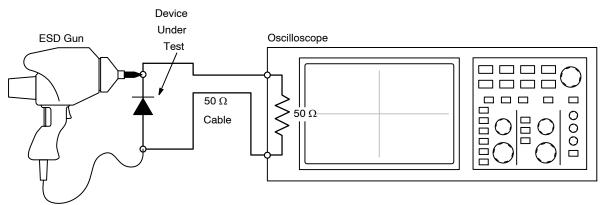
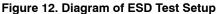


Figure 11. IEC61000-4-2 Spec

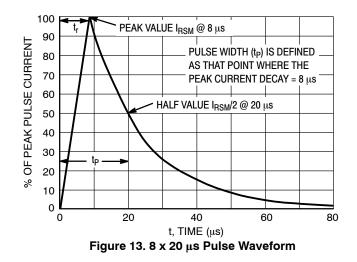




ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000–4–2 waveform. Since the IEC61000–4–2 was written as a pass/fail spec for larger systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage

at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.



Transmission Line Pulse (TLP) Measurement

Transmission Line Pulse (TLP) provides current versus voltage (I–V) curves in which each data point is obtained from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 14. TLP I–V curves of ESD protection devices accurately demonstrate the product's ESD capability because the 10s of amps current levels and under 100 ns time scale match those of an ESD event. This is illustrated in Figure 15 where an 8 kV IEC 61000–4–2 current waveform is compared with TLP current pulses at 8 A and 16 A. A TLP I–V curve shows the voltage at which the device turns on as well as how well the device clamps voltage over a range of current levels.

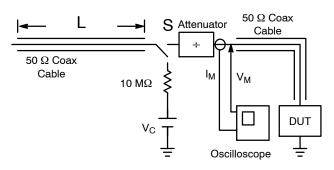


Figure 14. Simplified Schematic of a Typical TLP System

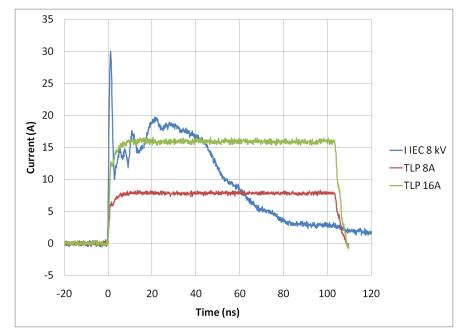


Figure 15. Comparison Between 8 kV IEC 61000-4-2 and 8 A and 16 A TLP Waveforms

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

onsemi

	2x0.32x0.2 SE 152AF SSUE C	4, 0.35P			DAT	E 08 AUG	à 2023
	AS	ME Y14 NTROL	INING (4.5M, 1 LING I	994.			
				MIL	LIMETER	S	
PIN 1			DIM	MIN.	NDM.	MAX.	
(ΠΡΤΙΠΝΔΙ.)			А	0.25	0.29	0.33	
TOP VIEW			A1	0.00		0.05	4
— A1			A2	0.14	0.24	0.34	-
// 0.05 C			b	0.22	0.25	0.28	-
			b2	(0.150 RE	F	4
			D	0.58	0.62	0.66	-
			E	0.28	0.32	0.36	-
SIDE VIEW			e	(0.355 BS	C	-
SIDE VIEW .			L2	0.17	0.20	0.23	4
			L3	0.74 <i></i>		F 2X 30	
		2Х	1	+[
= 2x l2 ⊕0.05@[C A B] B□TT□M VIEW	* F	or addit	JNTING	ormation	PRINT;	Ph-Free	2
GENERIC Technic MARKING DIAGRAM*		trategy he ON S echnique	y and soldering details, please download Semiconductor Soldering and Mounting ues Reference Manual, SOLDERRM/D.				wnload ting
PIN 1 XM							

X = Specific Device Code M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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 DESCRIPTION:
 X3DFN2 0.62x0.32x0.24, 0.35P
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